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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	40MHz
Connectivity	CSIO, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	23
Program Memory Size	56KB (56K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	6K × 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-WFQFN Exposed Pad
Supplier Device Package	32-QFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/s6e1a11b0agn2b000

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



A/D Converter (Max: 8 channels)

■12-bit A/D Converter

- □ Successive approximation type
- □ Conversion time: 0.8 µs @ 5 V (S6E1A1xC0A) / 2.0 µs (S6E1A1xB0A)
- □ Priority conversion available (2 levels of priority)
- □ Scan conversion mode
- □ Built-in FIFO for conversion data storage (for scan conversion: 16 steps, for priority conversion: 4 steps)

Base Timer (Max: 4 channels)

The operation mode of each channel can be selected from one of the following.

- ■16-bit PWM timer
- ■16-bit PPG timer
- ■16/32-bit reload timer
- ■16/32-bit PWC timer

General-purpose I/O Port

This series can use its pin as a general-purpose I/O port when it is not used for an external bus or a peripheral function. All ports can be set to fast general-purpose I/O ports or slow general-purpose I/O ports. In addition, this series has a port relocate function that can set to which I/O port a peripheral function can be allocated.

- ■All ports are Fast GPIO which can be accessed by 1cycle
- Capable of controlling the pull-up of each pin
- Capable of reading pin level directly
- ■Port relocate function
- ■Up to 37 fast general-purpose I/O ports @48pin package
- ■Certain ports are 5 V tolerant.

See "3. Pin Assignment" and "5. I/O Circuit Type" for details of such pins.

Dual Timer (32/16-bit Down Counter)

The Dual Timer consists of two programmable 32/16-bit down counters. The operation mode of each timer channel can be selected from one of the following.

- Free-running mode
- ■Periodic mode (= Reload mode)
- ■One-shot mode

Quadrature Position/Revolution Counter (QPRC)

The Quadrature Position/Revolution Counter (QPRC) is used to measure the position of the position encoder. In addition, it can be used as an up/down counter.

- The detection edge for the three external event input pins AIN, BIN and ZIN is configurable.
- 16-bit position counter
- ■16-bit revolution counter
- Two 16-bit compare registers

Multi-function Timer

The Multi-function Timer consists of the following blocks.

- ■16-bit free-run timer × 3 channels
- ■Input capture × 4 channels
- ■Output compare × 6 channels
- ■ADC start compare × 6 channel
- ■Waveform generator × 3 channels
- ■16-bit PPG timer × 3 channels

IGBT mode is contained.

The following function can be used to achieve the motor control.

- ■PWM signal output function
- ■DC chopper waveform output function
- Dead time function
- ■Input capture function
- ■ADC start function
- DTIF (motor emergency stop) interrupt function

Real-time Clock (RTC)

The Real-time Clock counts

year/month/day/hour/minute/second/day of the week from year 01 to year 99.

- The RTC can generate an interrupt at a specific time (year/month/day/hour/minute/second/day of the week) and can also generate an interrupt in a specific year, in a specific month, on a specific day, at a specific hour or at a specific minute.
- It has a timer interrupt function generating an interrupt upon a specific time or at specific intervals.
- It can keep counting while rewriting the time.
- It can count leap years automatically.



3. Pin Assignment



Note:

• The number after the underscore ("_") in pin names such as XXX_1 and XXX_2 indicates the relocated port number. For these pins, there are multiple pins that provide the same function for the same channel. Use the extended port function register (EPFR) to select the pin.



4. Pin Descriptions

List of Pin Functions

The number after the underscore ("_") in pin names such as XXX_1 and XXX_2 indicates the relocated port number. For these pins, there are multiple pins that provide the same function for the same channel.

Use the extended port function register (EPFR) to select the pin.

Pin no.					
LQFP-52	LQFP-48 QFN-48	LQFP-32 QFN-32	Pin name	I/O circuit type	Pin state type
1	1	-	VCC	-	
			P50		
			INT00_0		
2	2	-	AIN0_2	*	J
			SIN3_1		
			IC01_0		
			P51		
0	2		INT01_0	 *	
3	3	-	BIN0_2		J
			SOT3_1		
			P52		J
4	4		INT02_0	 *	
4	4	-	ZIN0_2	I	
			SCK3_1		
			P39		
6	5	-	DTTI0X_0	E	1
			ADTG_2		
			P3A		
			RTO00_0		
			TIOA0_1		
7	6	1	AIN0_3	— F	
1	0		SUBOUT_2	r	J
			RTCCO_2		
			INT03_0		
			SCK0_2		
			P3B		
			RTO01_0		
			TIOA1_1		
8	7	2	BIN0_3	F	J
			SOT0_2		
			INT04_0		
			SCS31_2		







Latch-up

Semiconductor devices are constructed by the formation of P-type and N-type areas on a substrate. When subjected to abnormally high voltages, internal parasitic PNPN junctions (called thyristor structures) may be formed, causing large current levels in excess of several hundred mA to flow continuously at the power supply pin. This condition is called latch-up.

CAUTION: The occurrence of latch-up not only causes loss of reliability in the semiconductor device, but can cause injury or damage from high heat, smoke or flame. To prevent this from happening, do the following:

- 1. Be sure that voltages applied to pins do not exceed the absolute maximum ratings. This should include attention to abnormal noise, surge levels, etc.
- 2. Be sure that abnormal current flows do not occur during the power-on sequence.

Observance of Safety Regulations and Standards

Most countries in the world have established standards and regulations regarding safety, protection from electromagnetic interference, etc. Customers are requested to observe applicable regulations and standards in the design of products.

Fail-Safe Design

Any semiconductor devices have inherently a certain rate of failure. You must protect against injury, damage or loss from such failures by incorporating safety design measures into your facility and equipment such as redundancy, fire protection, and prevention of over-current levels and other abnormal operating conditions.

Precautions Related to Usage of Devices

Cypress semiconductor devices are intended for use in standard applications (computers, office automation and other office equipment, industrial, communications, and measurement equipment, personal or household devices, etc.).

CAUTION: Customers considering the use of our products in special applications where failure or abnormal operation may directly affect human lives or cause physical injury or property damage, or where extremely high levels of reliability are demanded (such as aerospace systems, atomic energy controls, sea floor repeaters, vehicle operating controls, medical devices for life support, etc.) are requested to consult with sales representatives before such use. The company will not be responsible for damages arising from such use without prior approval.

6.2 Precautions for Package Mounting

Package mounting may be either lead insertion type or surface mount type. In either case, for heat resistance during soldering, you should only mount under Cypress's recommended conditions. For detailed information about mount conditions, contact your sales representative.

Lead Insertion Type

Mounting of lead insertion type packages onto printed circuit boards may be done by two methods: direct soldering on the board, or mounting by using a socket.

Direct mounting onto boards normally involves processes for inserting leads into through-holes on the board and using the flow soldering (wave soldering) method of applying liquid solder. In this case, the soldering process usually causes leads to be subjected to thermal stress in excess of the absolute ratings for storage temperature. Mounting processes should conform to Cypress recommended mounting conditions.

If socket mounting is used, differences in surface treatment of the socket contacts and IC lead surfaces can lead to contact deterioration after long periods. For this reason it is recommended that the surface treatment of socket contacts and IC leads be verified before mounting.

Surface Mount Type

Surface mount packaging has longer and thinner leads than lead-insertion packaging, and therefore leads are more easily deformed or bent. The use of packages with higher pin counts and narrower pin pitch results in increased susceptibility to open connections caused by deformed pins, or shorting due to solder bridges.

You must use appropriate mounting techniques. Cypress recommends the solder reflow method, and has established a ranking of mounting conditions for each product. Users are advised to mount packages in accordance with Cypress ranking of recommended conditions.



Lead-Free Packaging

CAUTION: When ball grid array (BGA) packages with Sn-Ag-Cu balls are mounted using Sn-Pb eutectic soldering, junction strength may be reduced under some conditions of use.

Storage of Semiconductor Devices

Because plastic chip packages are formed from plastic resins, exposure to natural environmental conditions will cause absorption of moisture. During mounting, the application of heat to a package that has absorbed moisture can cause surfaces to peel, reducing moisture resistance and causing packages to crack. To prevent, do the following:

- 1. Avoid exposure to rapid temperature changes, which cause moisture to condense inside the product. Store products in locations where temperature changes are slight.
- Use dry boxes for product storage. Products should be stored below 70% relative humidity, and at temperatures between 5°C and 30°C.

When you open Dry Package that recommends humidity 40% to 70% relative humidity.

- 3. When necessary, Cypress packages semiconductor devices in highly moisture-resistant aluminum laminate bags, with a silica gel desiccant. Devices should be sealed in their aluminum laminate bags for storage.
- 4. Avoid storing packages where they are exposed to corrosive gases or high levels of dust.

Baking

Packages that have absorbed moisture may be de-moisturized by baking (heat drying). Follow the Cypress recommended conditions for baking.

Condition: 125°C/24 h

Static Electricity

Because semiconductor devices are particularly susceptible to damage by static electricity, you must take the following precautions:

- 1. Maintain relative humidity in the working environment between 40% and 70%. Use of an apparatus for ion generation may be needed to remove electricity.
- 2. Electrically ground all conveyors, solder vessels, soldering irons and peripheral equipment.
- 3. Eliminate static body electricity by the use of rings or bracelets connected to ground through high resistance (on the level of 1 $M\Omega$).

Wearing of conductive clothing and shoes, use of conductive floor mats and other measures to minimize shock loads is recommended.

- 4. Ground all fixtures and instruments, or protect with anti-static measures.
- 5. Avoid the use of styrofoam or other highly static-prone materials for storage of completed board assemblies.



6.3 Precautions for Use Environment

Reliability of semiconductor devices depends on ambient temperature and other conditions as described above.

For reliable performance, do the following:

1. Humidity

Prolonged use in high humidity can lead to leakage in devices as well as printed circuit boards. If high humidity levels are anticipated, consider anti-humidity processing.

2. Discharge of Static Electricity

When high-voltage charges exist close to semiconductor devices, discharges can cause abnormal operation. In such cases, use anti-static measures or processing to prevent discharges.

3. Corrosive Gases, Dust, or Oil

Exposure to corrosive gases or contact with dust or oil may lead to chemical reactions that will adversely affect the device. If you use devices in such conditions, consider ways to prevent such exposure or to protect the devices.

4. Radiation, Including Cosmic Radiation

Most devices are not designed for environments involving exposure to radiation or cosmic radiation. Users should provide shielding as appropriate.

5. Smoke, Flame

CAUTION: Plastic molded devices are flammable, and therefore should not be used near combustible substances. If devices begin to smoke or burn, there is danger of the release of toxic gases.

Customers considering the use of Cypress products in other special environmental conditions should consult with sales representatives.



Notes on Power-on

Turn power on/off in the following order or at the same time.

Turning on : VBAT \rightarrow VCC VCC \rightarrow AVCC \rightarrow AVRH Turning off : VCC \rightarrow VBAT AVRH \rightarrow AVCC \rightarrow VCC

Serial Communication

There is a possibility to receive wrong data due to the noise or other causes on the serial communication. Therefore, design a printed circuit board so as to avoid noise.

Consider the case of receiving wrong data due to noise, perform error detection such as by applying a checksum of data at the end. If an error is detected, retransmit the data.

Differences in Features among the Products with Different Memory Sizes and between Flash Products and MASK Products

The electric characteristics including power consumption, ESD, latch-up, noise characteristics, and oscillation characteristics among the products with different memory sizes and between Flash products and MASK products are different because chip layout and memory structures are different.

If you are switching to use a different product of the same series, please make sure to evaluate the electric characteristics.

Pull-Up Function of 5V Tolerant I/O

Please do not input the signal more than VCC voltage at the time of Pull-Up function use of 5V tolerant I/O.



- *1 : Ta=+25°C,V_{CC}=3.0V
- *2 : Ta=+105°C,V_{CC}=5.5V
- *3 : All ports are fixed *4 : PCLK0=HCLK/8

- *5 : The frequency is set to 4MHz by trimming *6 : Flash sync down is set to FRWTR.RWT = 11 and FSYNDN.SD = 1111
- *7 : V_{CC}=2.7V *8 : When HCLK=4MHz, PLL OFF

Symbol				alue	Uni	
(Pin name)		Conditions	Тур	Max	t	Remarks
		Ta=25°C Vcc=3.0V LVD off	5.6	28	μA	*1
I _{ССН} (VCC)	STOP mode	Ta=25°C Vcc=5.0V LVD off	6.7	30	μA	*1
		Ta=105°C Vcc=5.5V LVD off	-	540	μA	*1
	Ta=25°C Vcc=3.0V 32kHz crystal oscillation LVD off	12	42	μA	*1	
I _{CCT} (VCC)	Sub timer mode	Ta=25°C Vcc=5.0V 32kHz crystal oscillation LVD off	13	44	μA	*1
		Ta=105°C Vcc=5.5V 32kHz crystal oscillation LVD off	-	730	μA	*1
		Ta=25°C Vcc=3.0V 32kHz crystal oscillation LVD off	9	36	μA	*1
I _{CCR} (VCC)	RTC mode	Ta=25°C Vcc=5.0V 32kHz crystal oscillation LVD off	10	38	μA	*1
		Ta=105°C Vcc=5.5V 32kHz crystal oscillation LVD off	-	570	μA	*1

*1:All ports are fixed.



LVD current

 $(V_{CC} = 2.7V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V, Ta = -40^{\circ}C \text{ to } + 105^{\circ}C)$

Parameter	Symbol	Pin	Conditions	Value		Unit	Remarks	
Falallielei	Symbol	name	Conditions	Тур	Max	Unit	Relliarks	
Low-Voltage detection circuit		NGG	At an anotion	0.13	0.3	μA	For occurrence of reset	
(LVD) power supply current	ICCLVD	VCC	At operation	0.13	0.3	μA	For occurrence of interrupt	

Flash memory current

 $(V_{CC} = 2.7V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V, Ta = -40^{\circ}C \text{ to } + 105^{\circ}C)$

Parameter	Symbol	Pin	Conditions		lue	Unit	Remarks	
i arameter	eyniser	name	oonaliono	Typ Max		•		
Flash memory write/erase current	I _{CCFLASH}	VCC	At Write/Erase	9.5	11.2	mA		

A/D convertor current (S6E1A1xC0A)

 $(V_{CC} = 2.7V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V, Ta = -40^{\circ}C \text{ to } + 105^{\circ}C)$

Parameter	Symbol	Pin	Conditions	Va	lue	Unit	Remarks	
Farameter	Symbol	name	Conditions	Тур	Max	Unit		
Power supply		AVCC	At operation	0.7	0.9	mA		
current	ICCAD	AVCC	At stop	0.13	13	μA		
Reference power supply			At operation	1.1	1.97	mA	AVRH=5.5V	
current (AVRH)	ICCAVRH	AVRH	At stop	0.1	1.7	μA		

A/D convertor current (S6E1A1xB0A)

 $(V_{CC} = 2.7V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V, Ta = -40^{\circ}C \text{ to } + 105^{\circ}C)$

Parameter	Symbol	Pin	Conditions	Value		Unit	Remarks	
Falameter	Symbol	name	Conditions	Тур	Max	Unit	Remarks	
Power supply	1	AVCC	At operation	1.8	2.87	mA		
current	ICCAD	AVCC	At stop	0.23	14.7	μA		

Peripheral current dissipation

Clock	Peripheral	Conditions		Frequen	cy (MHz)	Unit	Remarks
system	renpheral	Conditions	4	8	20	40	Onic	Remarks
HCLK	GPIO	At all ports operation	0.11	0.22	0.55	1.10	m۸	
HULK	DMAC	At 2ch operation	0.05	0.11	0.25	0.51	mA	
	Base timer	At 4ch operation	0.03	0.05	0.15	0.30		
	Multi-functional timer/PPG	At 1unit/4ch operation	0.14	0.28	0.68	1.38		
PCLK1	Quadrature position/Revolution counter	At 1unit operation	0.02	0.04	0.11	0.22	mA	
	ADC	At 1unit operation	0.07	0.14	0.37	0.73		
	Multi-function serial	At 1ch operation	0.15	0.31	0.77	1.54		



12.3.2 Pin Characteristics

Parameter	Symbol	Pin name	Conditions		Value		Unit	Remarks
i arameter	Cymbol		Conditions	Min	Тур	Max	Onic	Remarks
"H" level input voltage V _{IHS}	CMOS hysteresis input pin, MD0, PE0	-	V _{CC} × 0.8	-	V _{CC} + 0.3	V		
input)		5V tolerant input pin	-	V _{CC} × 0.8	-	V _{SS} + 5.5	V	
"L" level input voltage (hysteresis	V _{ILS}	CMOS hysteresis input pin, MD0, PE0	-	V _{SS} - 0.3	-	V _{CC} × 0.2	V	
input)	5V tolerant input pin	-	V _{SS} - 0.3	-	V _{CC} × 0.2	V		
"H" level output voltage	4 mA type	$V_{CC} \ge 4.5 V,$ $I_{OH} = -4 mA$ $V_{CC} < 4.5 V,$ $I_{OH} = -2 mA$	V _{CC} - 0.5	-	V _{cc}	v		
	VOH	12 mA type	$V_{CC} \ge 4.5 V,$ $I_{OH} = -12 mA$ $V_{CC} < 4.5 V,$ $I_{OH} = -8 mA$	- V _{CC} - 0.5	-	V _{cc}	v	
"L" level	Vol	4 mA type	$V_{CC} \ge 4.5 \text{ V},$ $I_{OL} = 4 \text{ mA}$ $V_{CC} < 4.5 \text{ V},$ $I_{OL} = 2 \text{ mA}$	- V _{ss}	-	0.4	v	
output voltage	VOL	12 mA type	$V_{CC} \ge 4.5 V,$ $I_{OL} = 12 mA$ $V_{CC} < 4.5 V,$ $I_{OL} = 8 mA$	- V _{SS}	-	0.4	V	
Input leak current	I _{IL}	-	-	- 5	-	+ 5	μA	
Pull-up resistance	R _{PU}	Pull-up pin	V _{CC} ≥ 4.5 V	33	50	90	kΩ	
value			V_{CC} < 4.5 V	-	-	180		
Input capacitance	C _{IN}	Other than VCC, VSS, AVCC, AVSS, AVRH	-	-	5	15	pF	

(V_{CC} =AV_{CC} = 2.7 V to 5.5 V, V_{SS} = AV_{SS} = 0 V, Ta = - 40°C to + 105°C)





















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External clock (EXT = 1): asynchronous only

	= AV _{CC} = 2.7 V to 5.5 V, V_{SS} = AV _{SS} = 0	V, Ta =	- 40°C to + 105	5°C)
	Value			

Parameter	Symbol	Conditions		Unit	Remarks	
raiameter	Symbol	Conditions	Min	Max	Onne	itema ka
Serial clock "L" pulse width	t _{SLSH}		t _{CYCP} + 10	-	ns	
Serial clock "H" pulse width	t _{SHSL}	$C_{L} = 30 pF$	t _{CYCP} + 10	-	ns	
SCK falling time	tF	$C_L = 30 \text{ pr}$	-	5	ns	
SCK rising time	tR		-	5	ns	













12.7 Flash Memory Write/Erase Characteristics

 $(V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}, \text{ Ta} = -40^{\circ}\text{C to} + 105^{\circ}\text{C})$

Paramete			Value		Unit	Remarks	
Faialliete	FI	Min	Тур	Max	Unit	Kellidi K5	
Sector erase time	Large sector	-	0.7	2.2		The sector erase time includes the time of writing prior to internal erase.	
Sector erase time	Small sector		0.3	0.9	s		
Halfword (16-bit) write	e time	-	30	528	μs	The halfword (16-bit) write time excludes the system-level overhead.	
Chip erase time		-	2.6	8	s	The chip erase time includes the time of writing prior to internal erase.	

Write/erase cycle and data hold time

Write/erase cycle	Data hold time (year)	Remarks
1,000	20*	
10,000	10*	

*: This value was converted from the result of a technology reliability assessment. (This value was converted from the result of a high temperature accelerated test using the Arrhenius equation with the average temperature value being + 85°C).





Operation example of return from low power consumption mode (by internal resource reset*)

*: Internal resource reset is not included in return factor by the kind of Low-Power consumption mode.

Notes:

- The return factor is different in each Low-Power consumption modes.
- See "Chapter: Low Power Consumption Mode" and "Operations of Standby Modes" in FM0+ Family PERIPHERAL MANUAL.
 When interrupt recoveries, the operation mode that CPU recoveries depends on the state before the Low-Power consumption mode transition. See "CHAPTER: Low Power Consumption Mode" in "FM0+ Family PERIPHERAL MANUAL".
- The time during the power-on reset/low-voltage detection reset is excluded. See "12.4.7 Power-on Reset Timing " for the detail on the time during the power-on reset/low -voltage detection reset.
- When in recovery from reset, CPU changes to the high-speed CR run mode. When using the main clock or the PLL clock, it is necessary to add the main clock oscillation stabilization wait time or the main PLL clock stabilization wait time.
- The internal resource reset means the watchdog reset and the CSV reset.



14. Package Dimensions









